

UNR911xJ Series (UN911xJ Series)

Silicon PNP epitaxial planar type

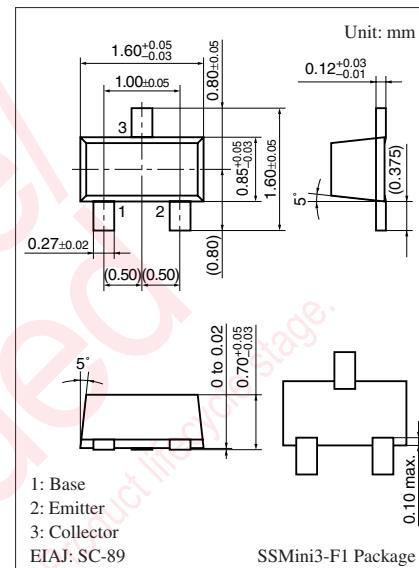
For digital circuits

■ Features

- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- SS-Mini type package, allowing automatic insertion through tape packing.

■ Resistance by Part Number

	Marking Symbol	(R ₁)	(R ₂)
• UNR9110J (UN9110J)	6L	47 kΩ	—
• UNR9111J (UN9111J)	6A	10 kΩ	10 kΩ
• UNR9112J (UN9112J)	6B	22 kΩ	22 kΩ
• UNR9113J (UN9113J)	6C	47 kΩ	47 kΩ
• UNR9114J (UN9114J)	6D	10 kΩ	47 kΩ
• UNR9115J (UN9115J)	6E	10 kΩ	—
• UNR9116J (UN9116J)	6F	4.7 kΩ	—
• UNR9117J (UN9117J)	6H	22 kΩ	—
• UNR9118J (UN9118J)	6I	0.51 kΩ	5.1 kΩ
• UNR9119J (UN9119J)	6K	1 kΩ	10 kΩ
• UNR911AJ	6X	100 kΩ	100 kΩ
• UNR911BJ	6Y	100 kΩ	—
• UNR911CJ	6Z	—	47 kΩ
• UNR911DJ (UN911DJ)	6M	47 kΩ	10 kΩ
• UNR911EJ (UN911EJ)	6N	47 kΩ	22 kΩ
• UNR911FJ (UN911FJ)	6O	4.7 kΩ	10 kΩ
• UNR911HJ (UN911HJ)	6P	2.2 kΩ	10 kΩ
• UNR911LJ (UN911LJ)	6Q	4.7 kΩ	4.7 kΩ
• UNR911MJ	EI	2.2 kΩ	47 kΩ
• UNR911NJ	EW	4.7 kΩ	47 kΩ
• UNR911TJ (UN911TJ)	EY	22 kΩ	47 kΩ
• UNR911VJ	FC	2.2 kΩ	2.2 kΩ



Internal Connection

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-50	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Collector current	I _C	-100	mA
Total power dissipation	P _T	125	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

Note) The part numbers in the parenthesis show conventional part number.

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

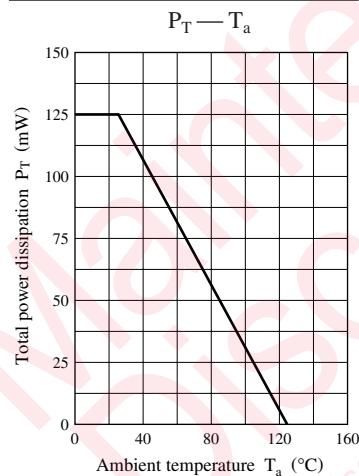
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			-0.1	μA
Collector-base cutoff current (Emitter open)	I_{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			-0.5	μA
Emitter-base cutoff current (Base open)	I_{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$		-0.01		mA
UNR9110J/9113J/911AJ				-0.1		
(Collector open)	UNR9112J/9114J/911DJ/ 911EJ/911MJ/911NJ/911TJ			-0.2		
UNR9111J				-0.5		
UNR911FJ/911HJ				-1.0		
UNR9119J				-1.5		
UNR9118J/911CJ/911LJ/911VJ				-2.0		
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	6	20		—
UNR911VJ			20			
UNR9118J/911LJ			30			
UNR9119J/911DJ/911FJ/911HJ			35			
UNR9111J			60			
UNR9112J/911EJ			80			
UNR9113J/9114J/911AJ/ 911CJ/911MJ			80	400		
UNR911NJ/911TJ			160	460		
UNR9110J/9115J/9116J/ 9117J/911BJ						
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			-0.25	V
UNR911VJ		$I_C = -10 \text{ mA}, I_B = -1.5 \text{ mA}$				
Output voltage high-level	V_{OH}	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V_{OL}	$V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			-0.2	V
UNR9113J/911BJ		$V_{CC} = -5 \text{ V}, V_B = -3.5 \text{ V}, R_L = 1 \text{ k}\Omega$				
UNR911DJ		$V_{CC} = -5 \text{ V}, V_B = -10 \text{ V}, R_L = 1 \text{ k}\Omega$				
UNR911EJ		$V_{CC} = -5 \text{ V}, V_B = -6 \text{ V}, R_L = 1 \text{ k}\Omega$				
UNR911AJ		$V_{CC} = -5 \text{ V}, V_B = -5 \text{ V}, R_L = 1 \text{ k}\Omega$				
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
UNR9113J		$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		150		
UNR911AJ		$V_{CB} = -10 \text{ V}, I_E = 2 \text{ mA}, f = 200 \text{ MHz}$		80		
UNR911CJ		$V_{CB} = -10 \text{ V}, I_E = 2 \text{ mA}, f = 200 \text{ MHz}$		150		
Input resistance	R_I		-30%	0.51	+30%	k Ω
UNR9118J				1.0		
UNR9119J				2.2		
UNR911HJ/911MJ/911VJ				4.7		
UNR9116J/911FJ/911LJ/911NJ				10		
UNR9111J/9114J/9115J				22		
UNR9112J/9117J/911TJ				47		
UNR9110J/9113J/911DJ/911EJ				100		
UNR911AJ/911BJ						

■ Electrical Characteristics (continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

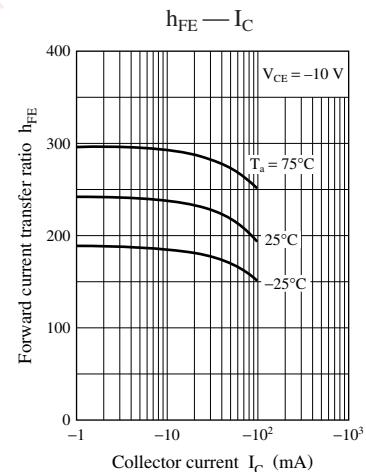
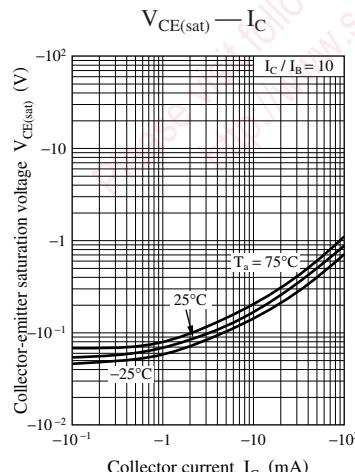
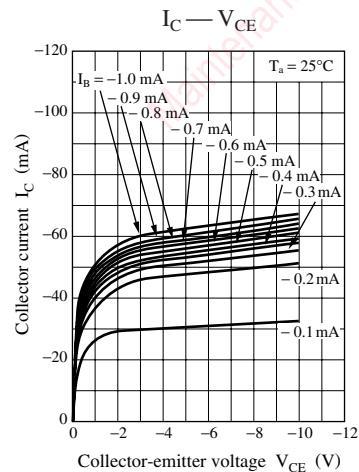
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Emitter-base resistance	UNR911CJ	R_2	-30%	47	+30%	kΩ
Resistance ratio	UNR911MJ	R_1/R_2		0.047		—
	UNR911NJ			0.1		
	UNR9118J/9119J		0.08	0.10	0.12	
	UNR9114J		0.17	0.21	0.25	
	UNR911HJ		0.17	0.22	0.27	
	UNR911TJ			0.47		
	UNR911FJ		0.37	0.47	0.57	
	UNR911AJ/911VJ			1.0		
	UNR911JJ/9112J/9113J/911LJ		0.8	1.0	1.2	
	UNR911EJ		1.70	2.14	2.60	
	UNR911DJ		3.7	4.7	5.7	

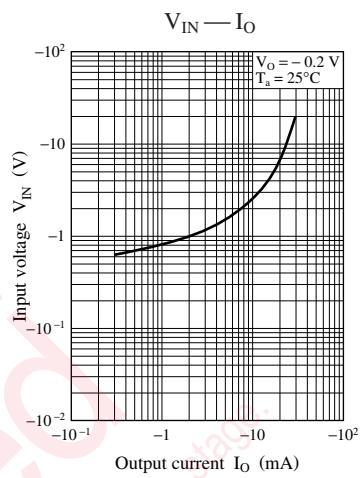
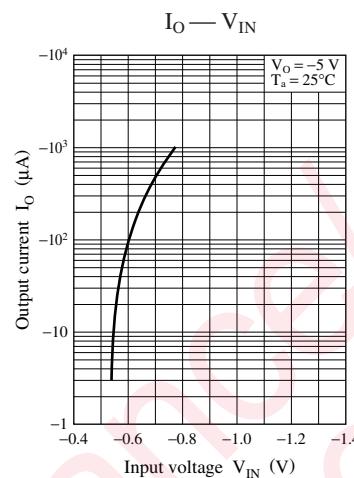
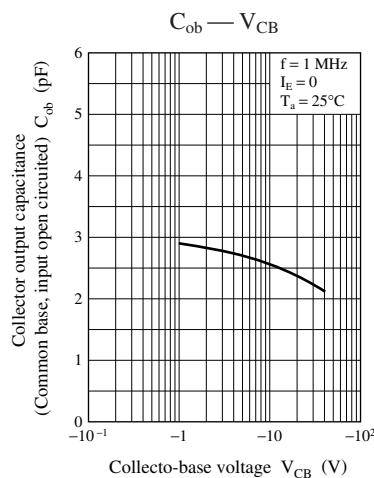
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

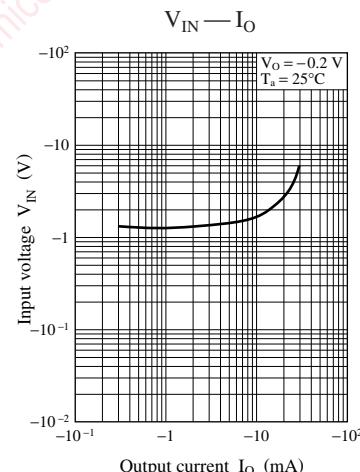
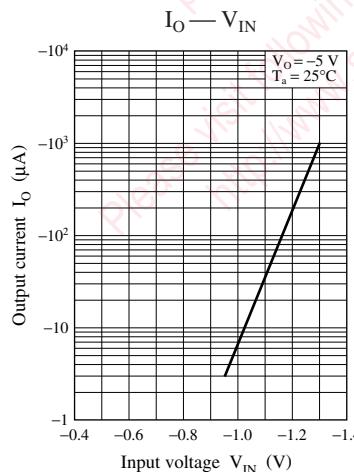
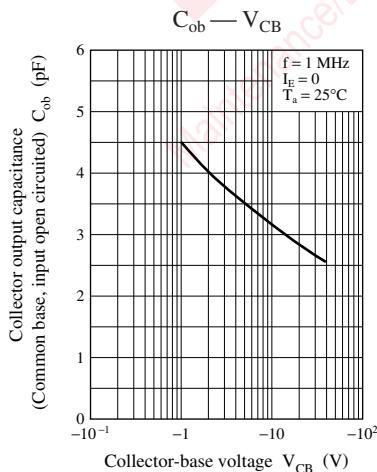
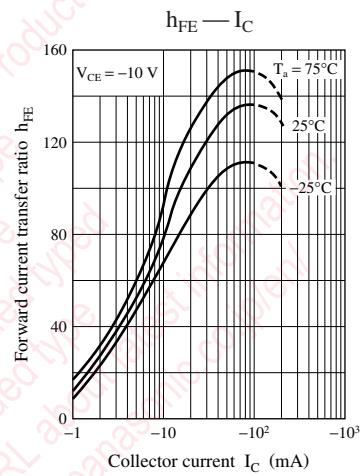
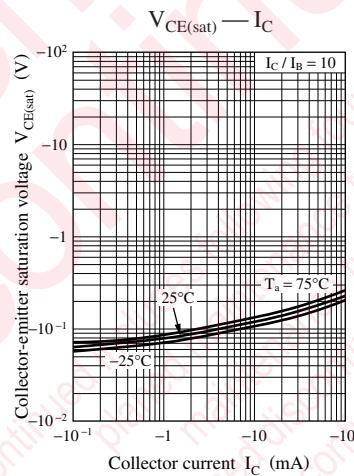
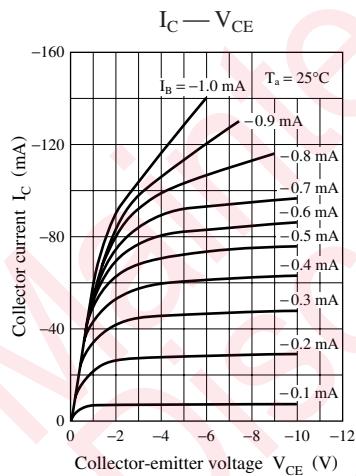


Characteristics charts of UNR9110J

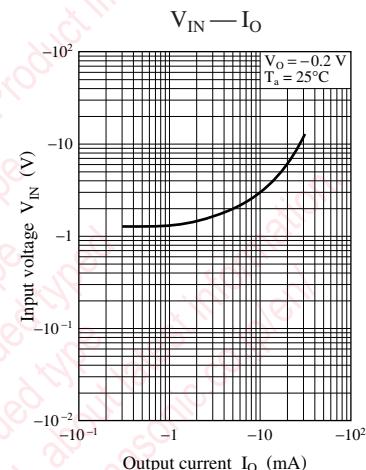
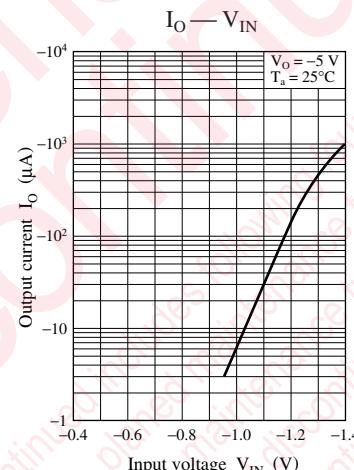
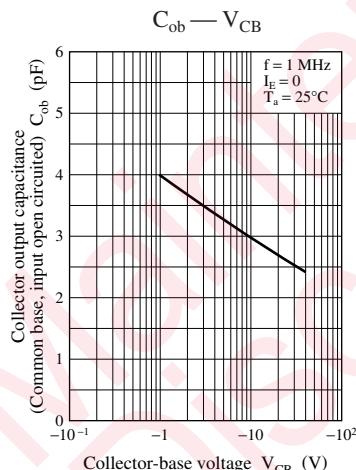
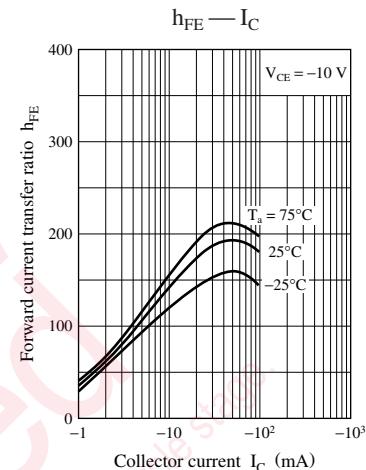
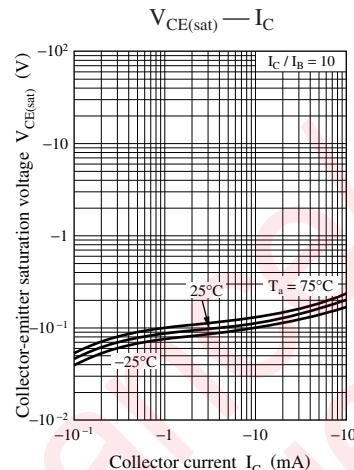
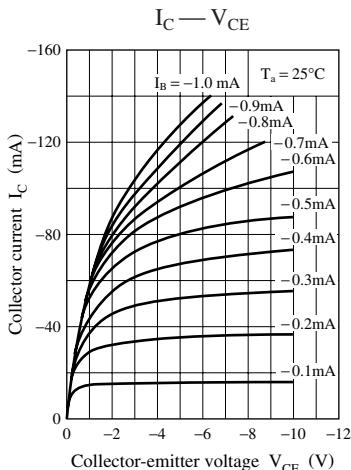




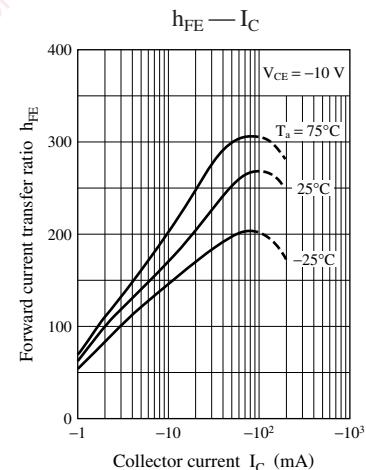
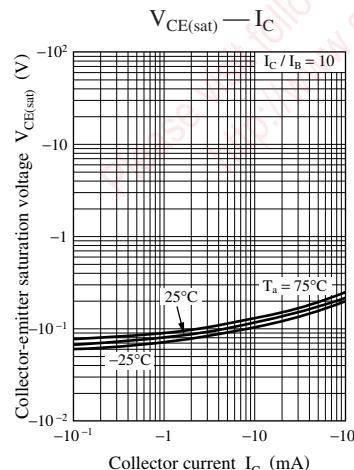
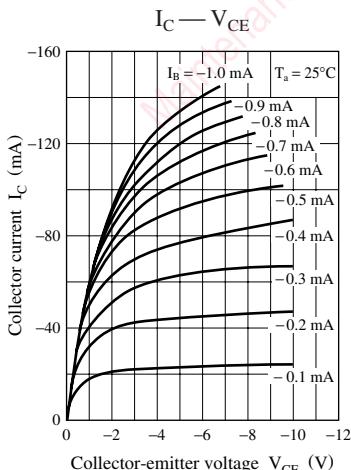
Characteristics charts of UNR9111J

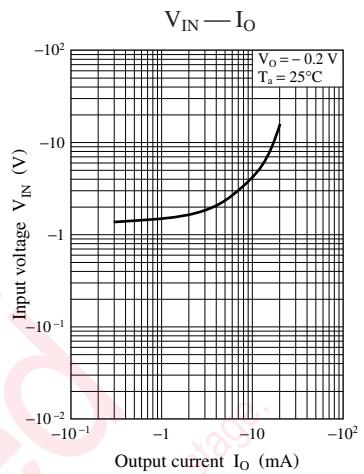
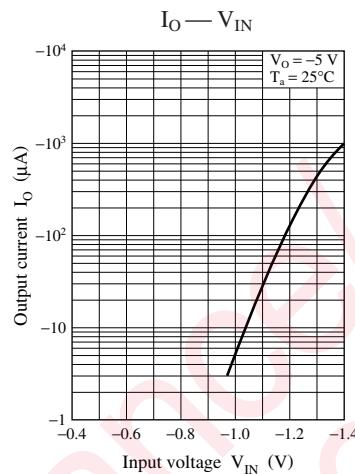
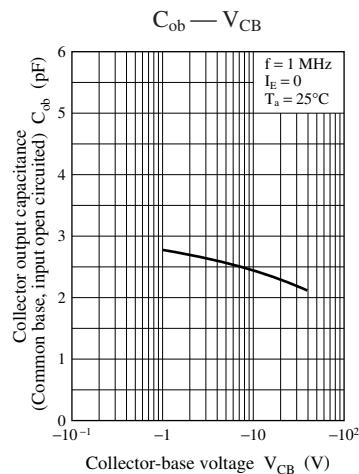


Characteristics charts of UNR9112J

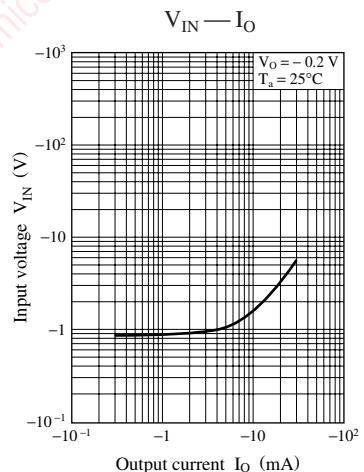
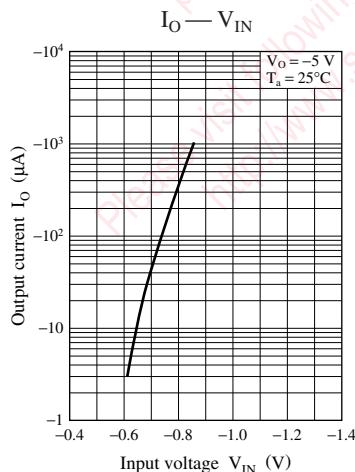
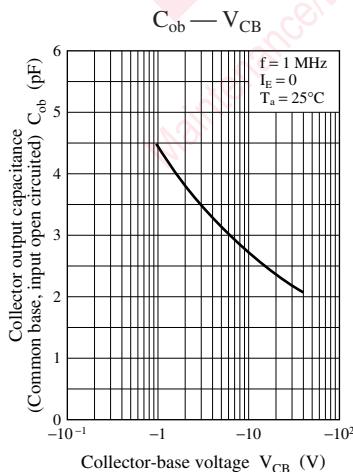
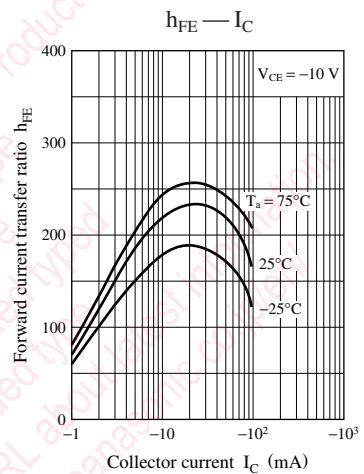
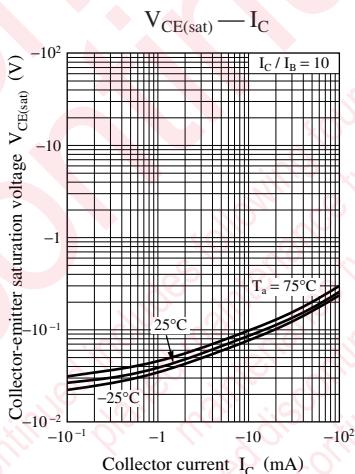
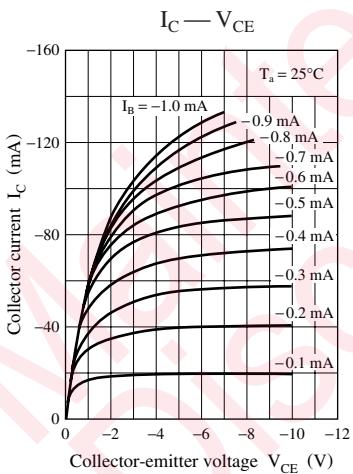


Characteristics charts of UNR9113J

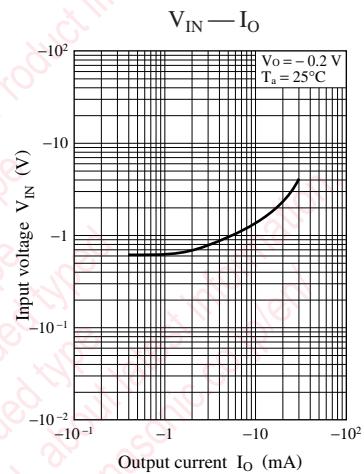
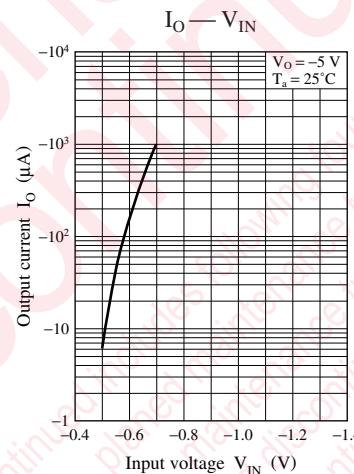
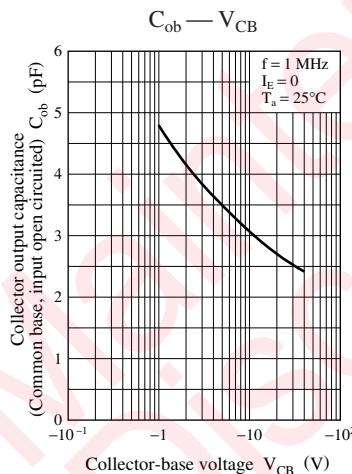
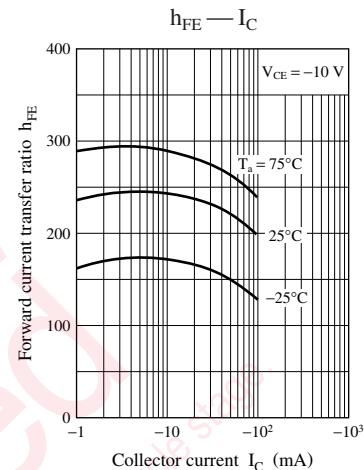
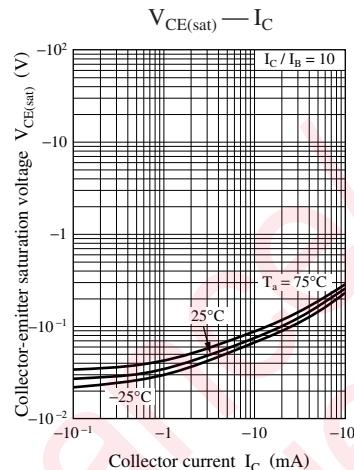
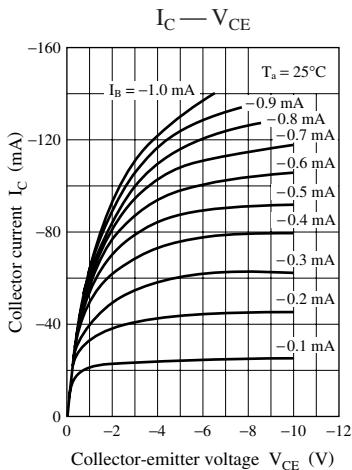




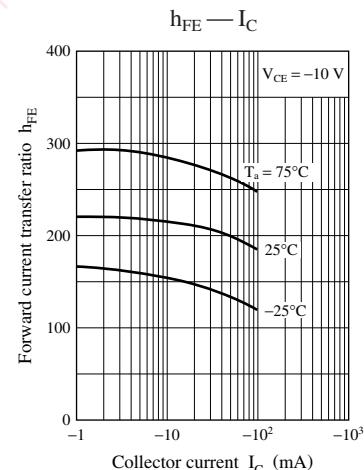
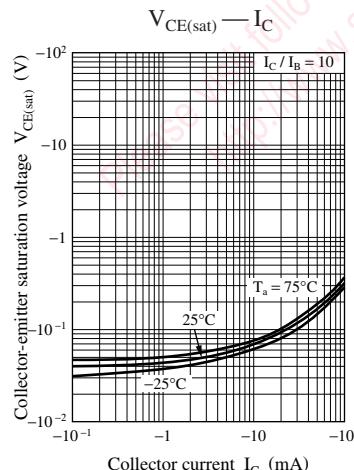
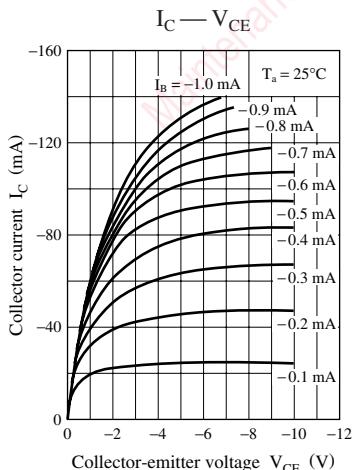
Characteristics charts of UNR9114J

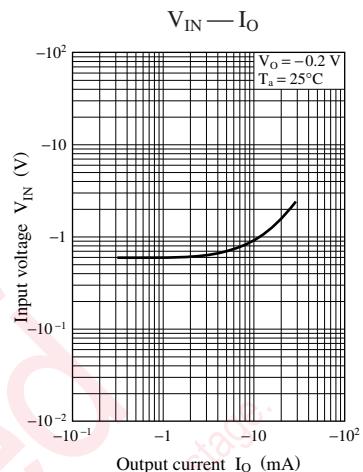
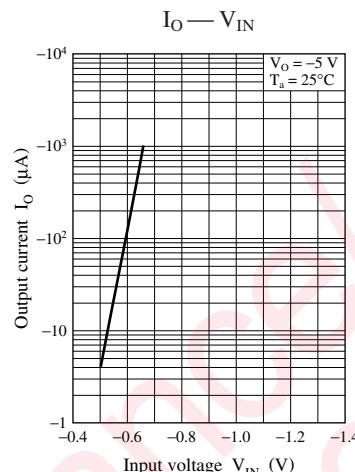
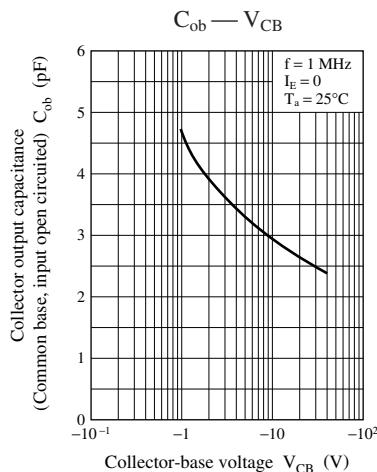


Characteristics charts of UNR9115J

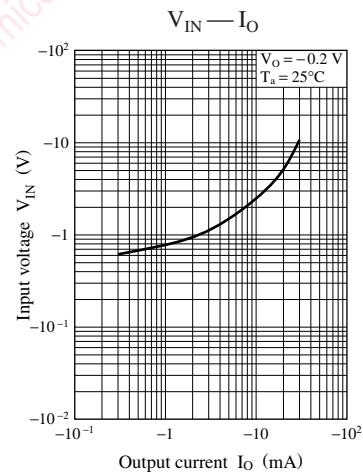
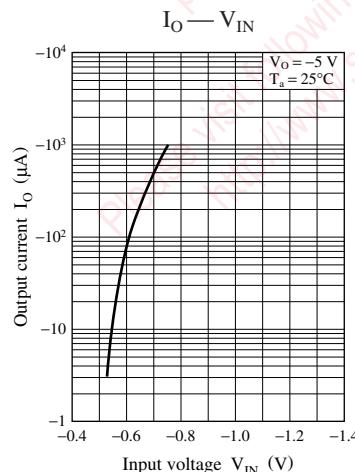
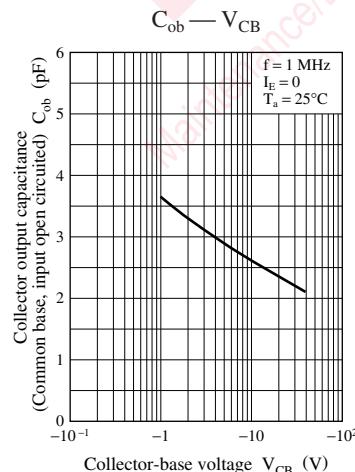
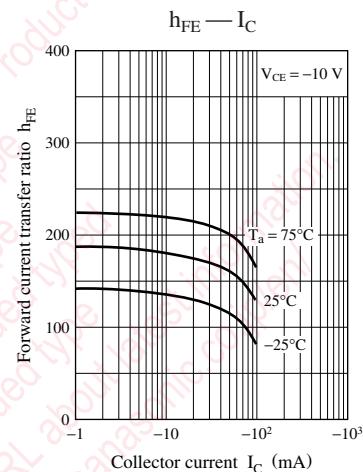
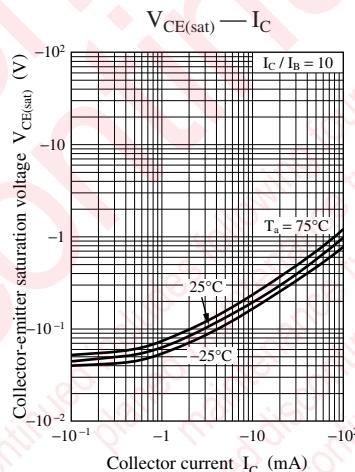
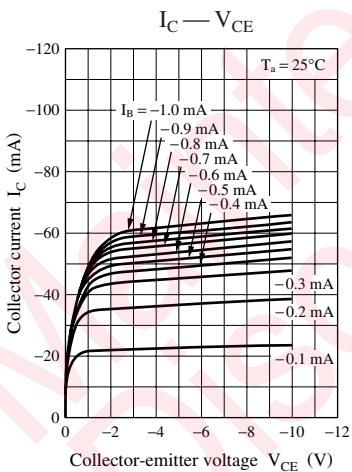


Characteristics charts of UNR9116J

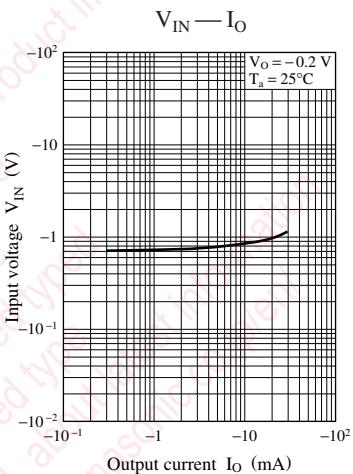
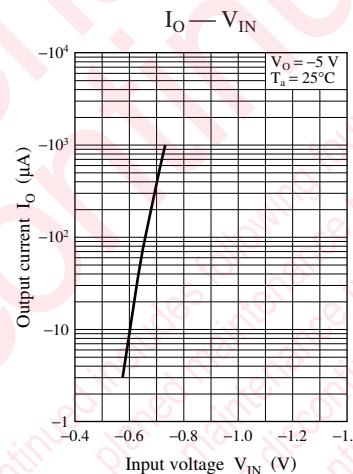
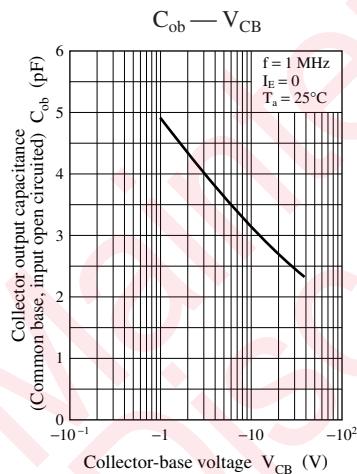
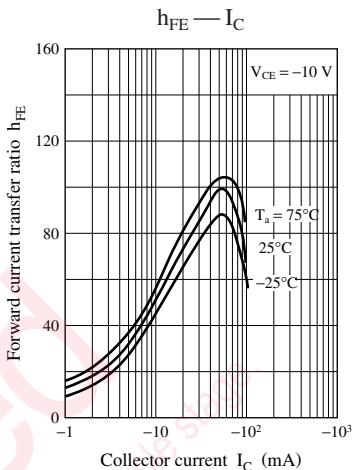
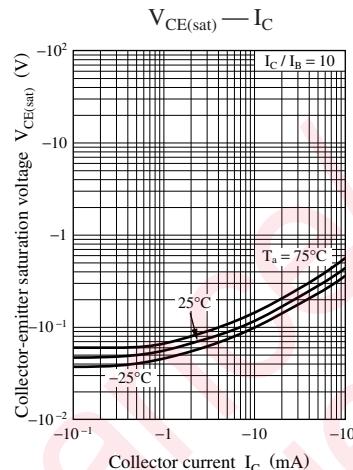
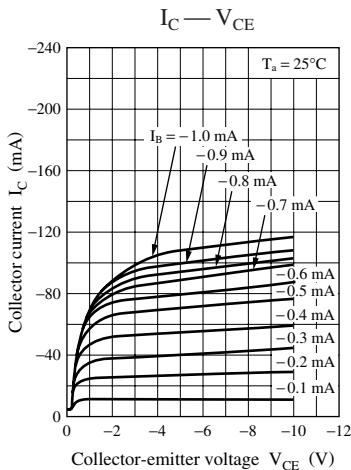




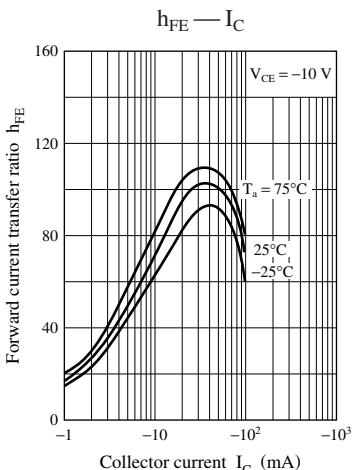
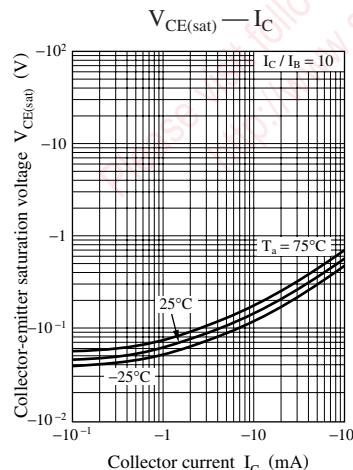
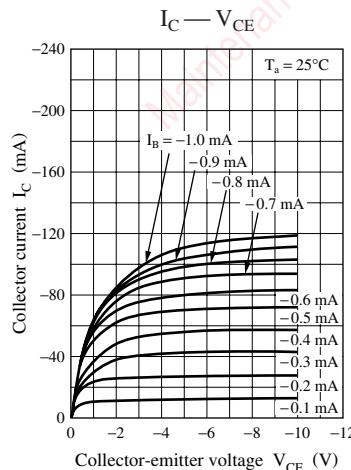
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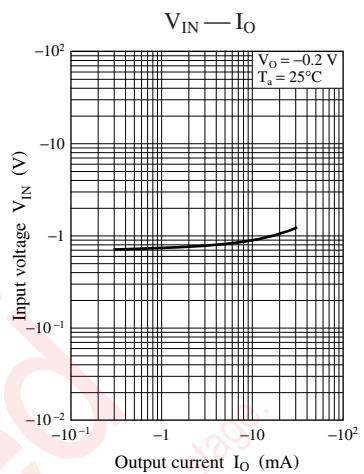
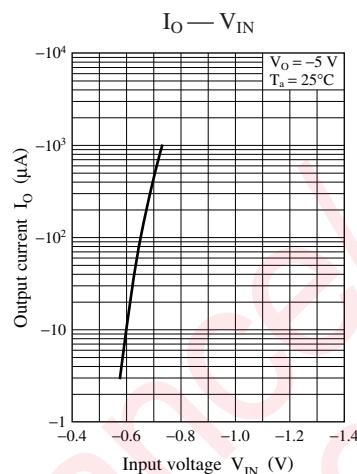
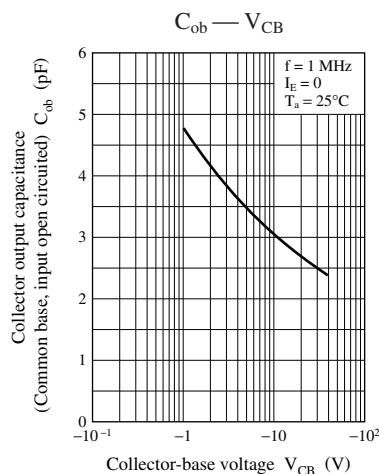


Characteristics charts of UNR9118J

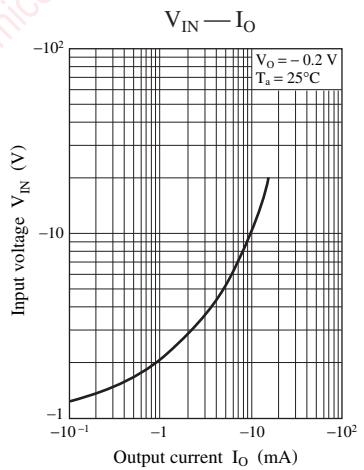
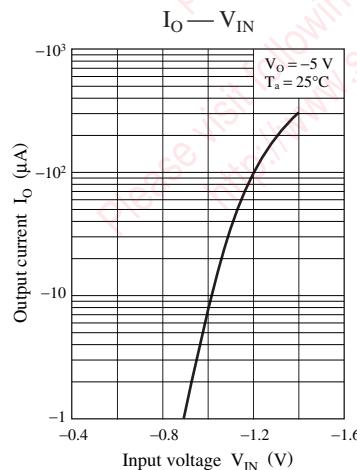
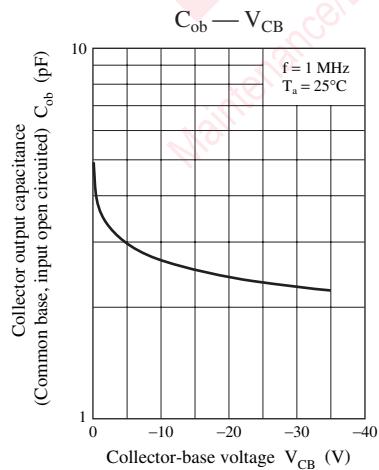
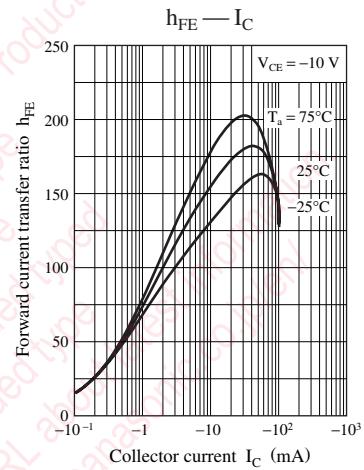
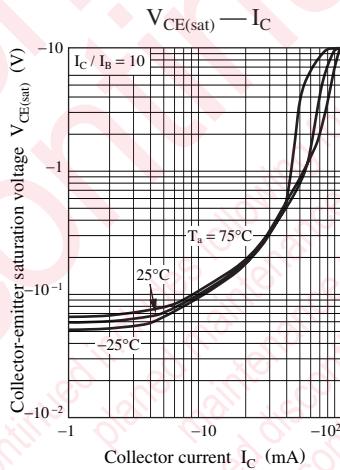
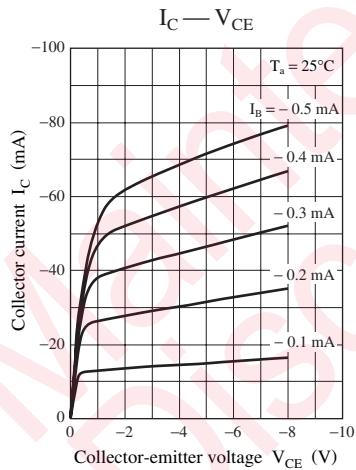


Characteristics charts of UNR9119J

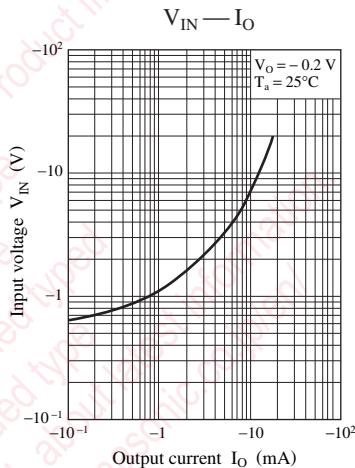
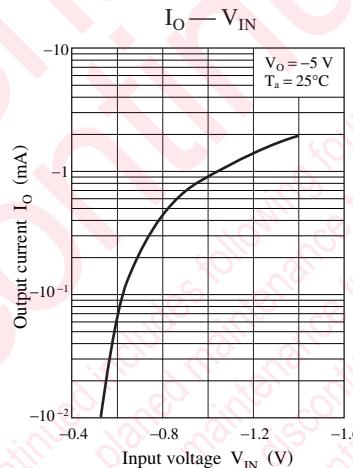
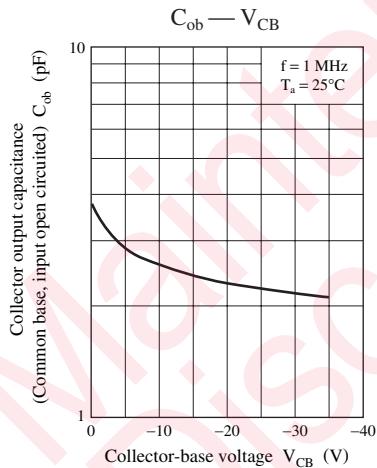
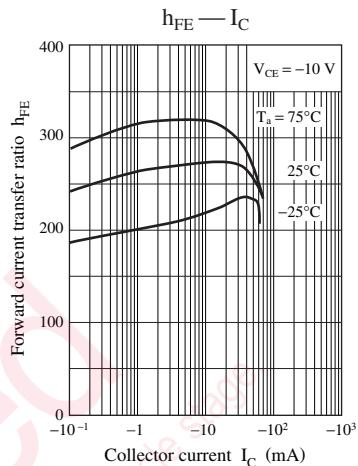
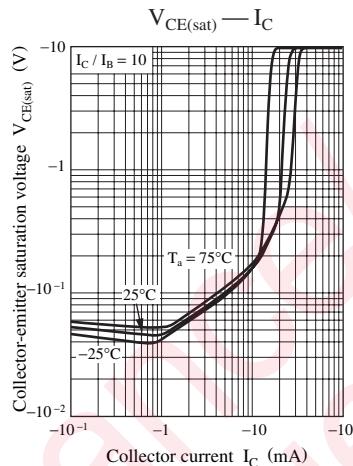
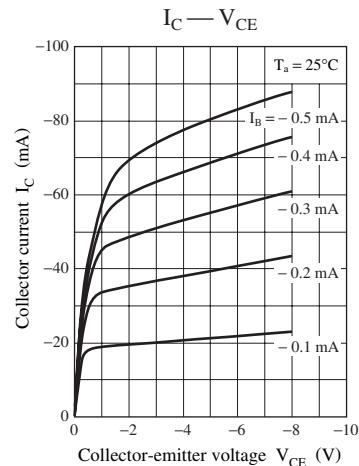




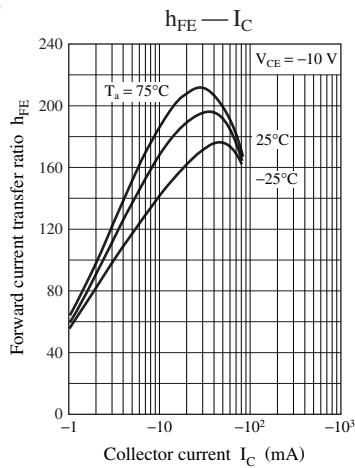
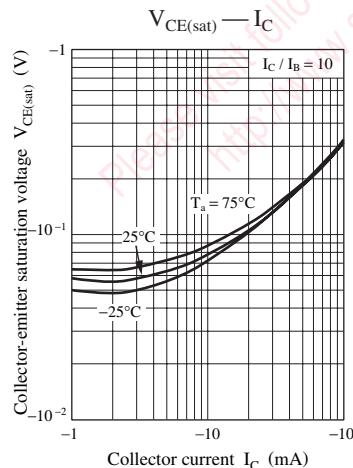
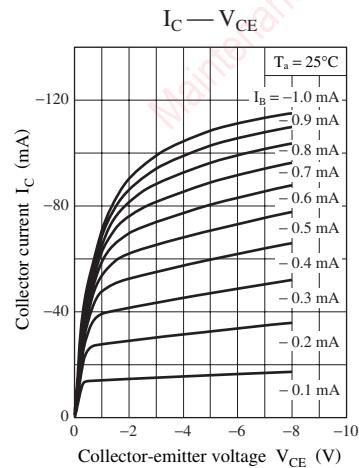
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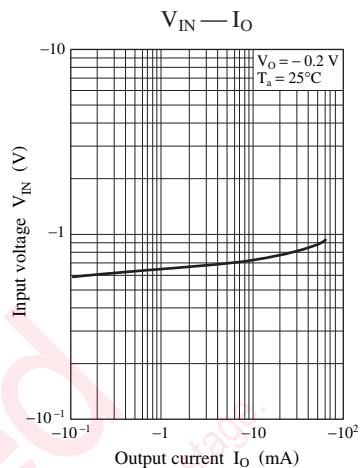
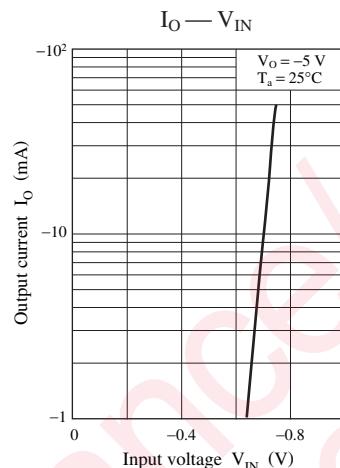
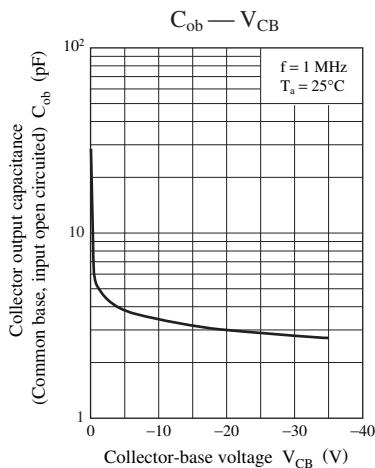


Characteristics charts of UNR911BJ

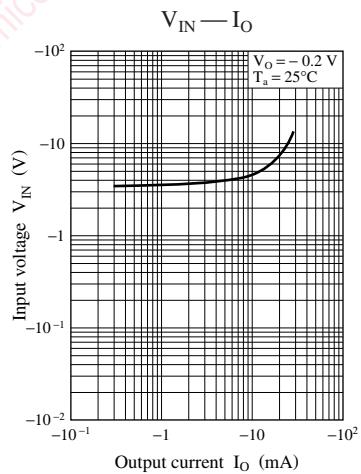
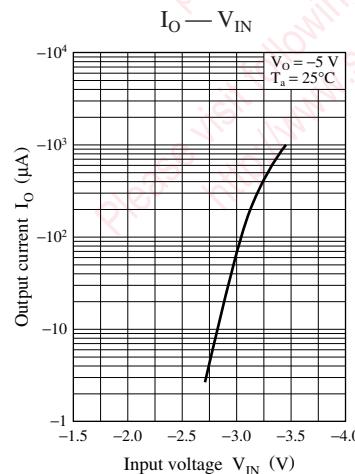
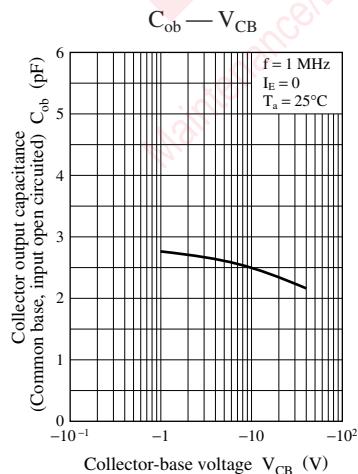
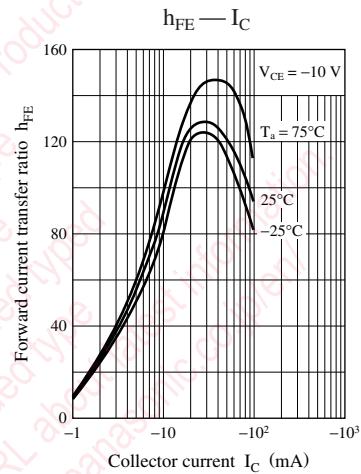
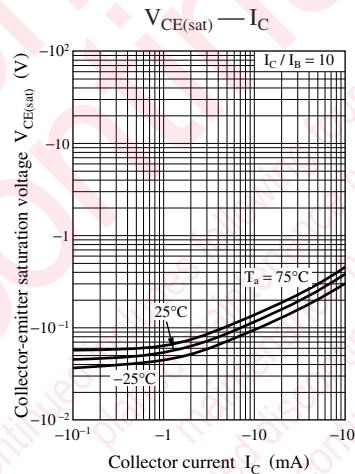
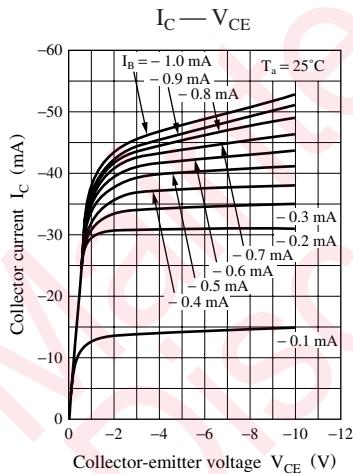


Characteristics charts of UNR911CJ

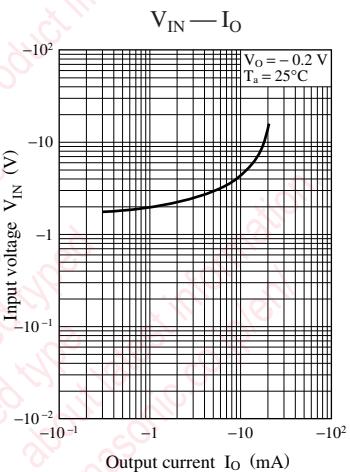
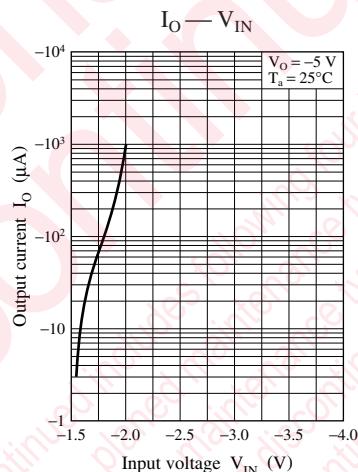
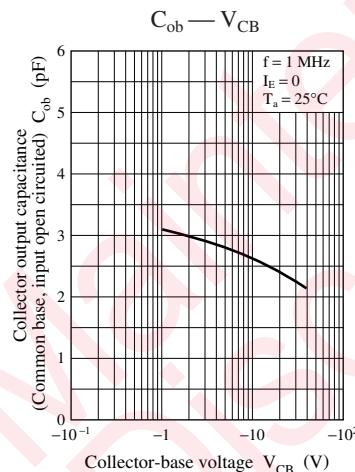
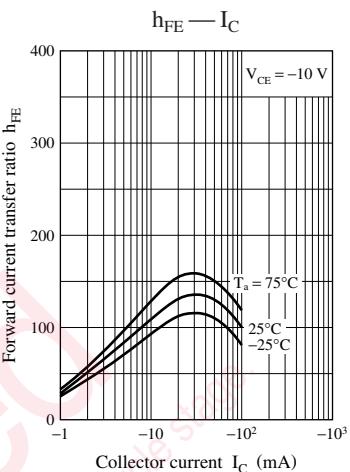
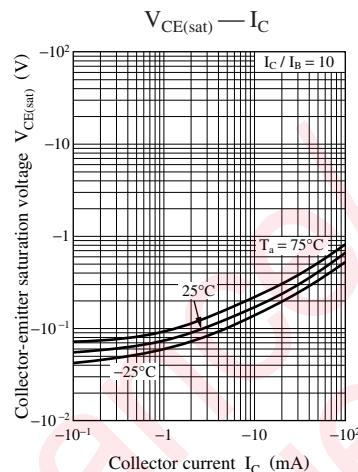
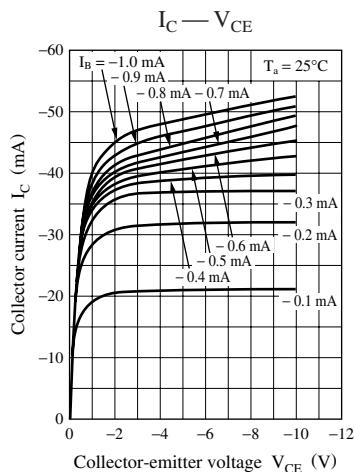




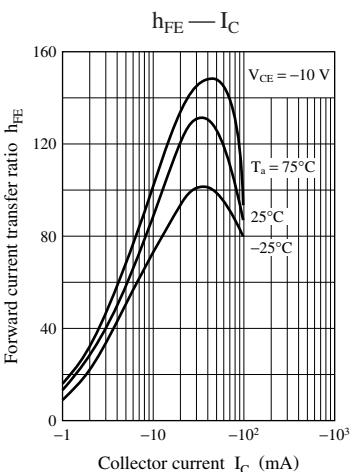
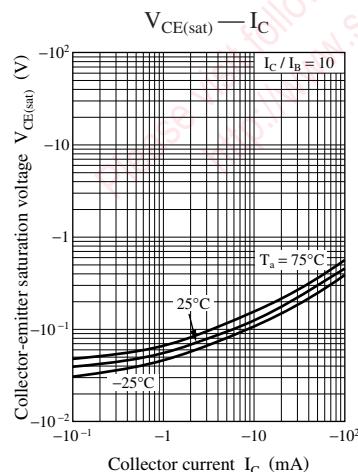
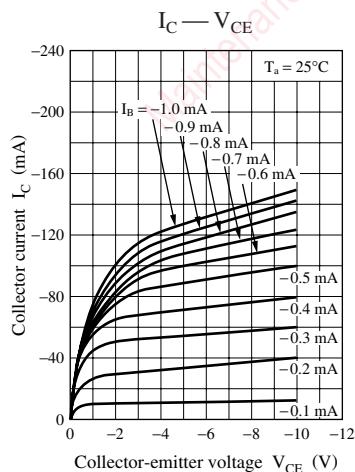
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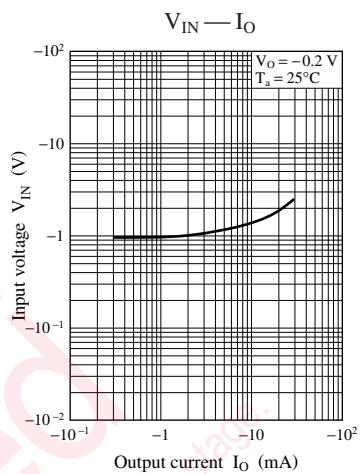
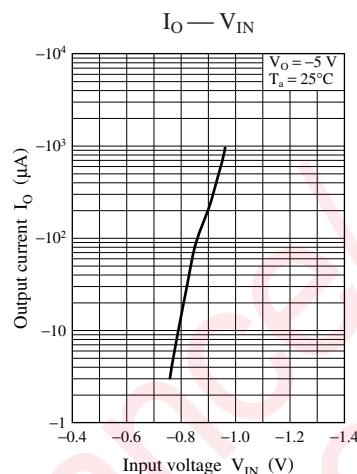
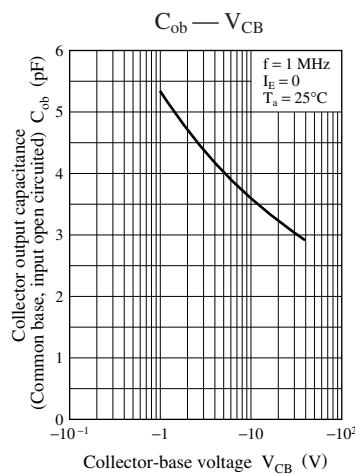


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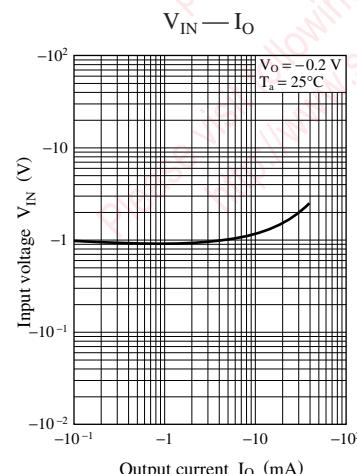
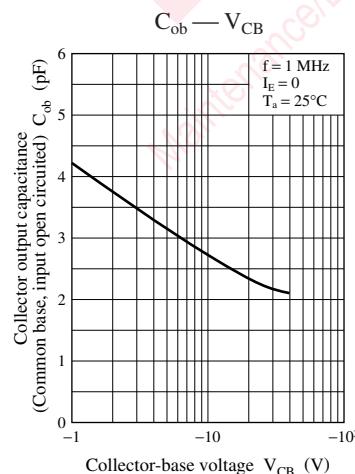
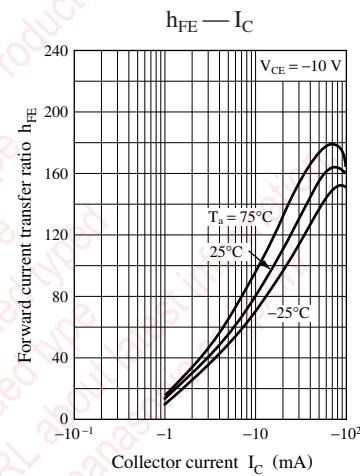
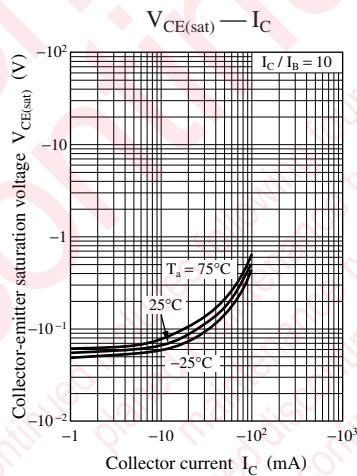
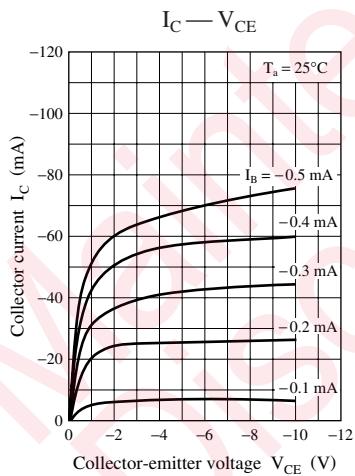


Characteristics charts of UNR911FJ

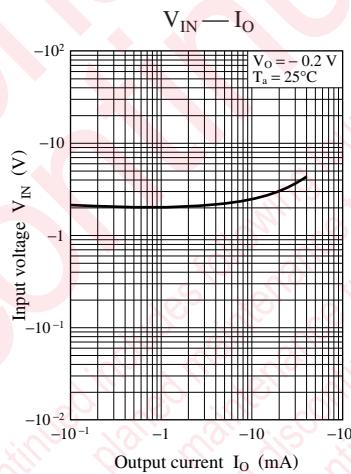
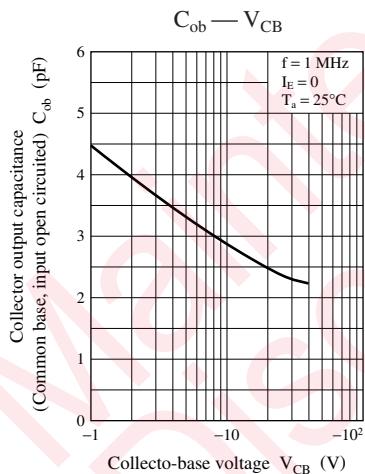
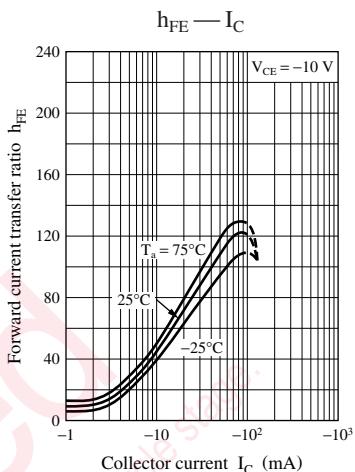
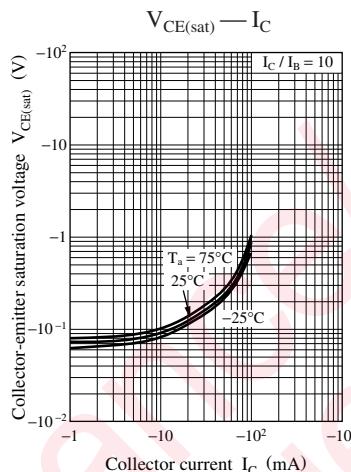
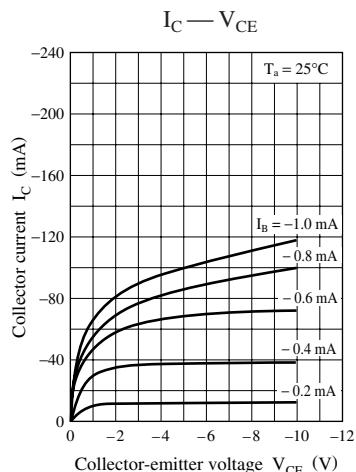




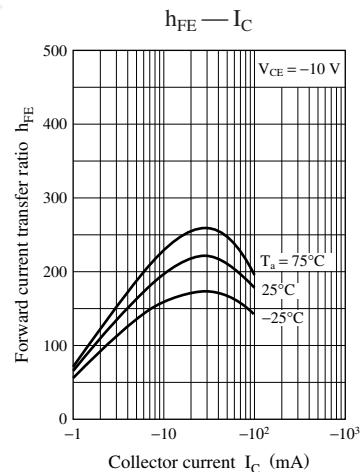
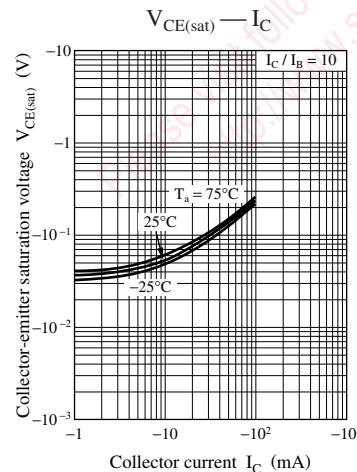
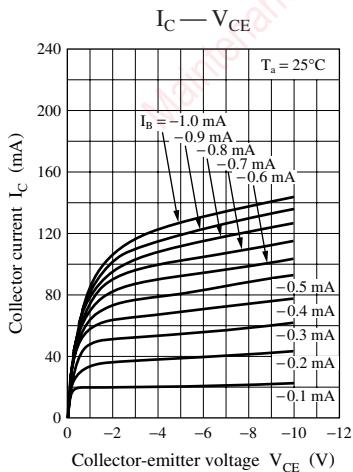
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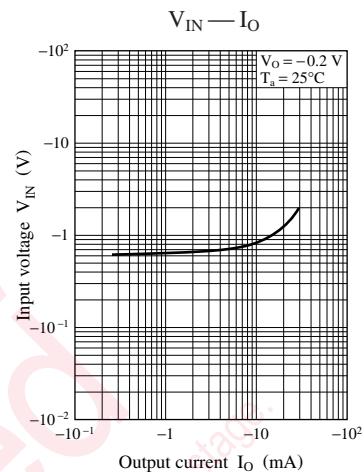
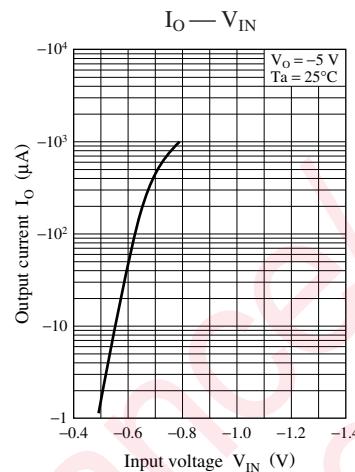
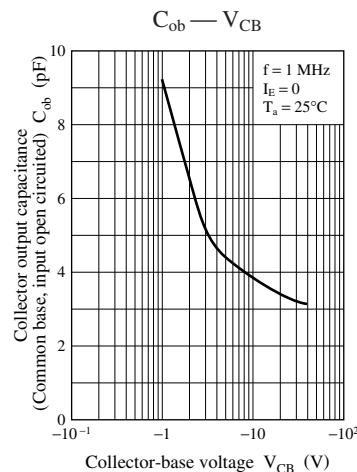


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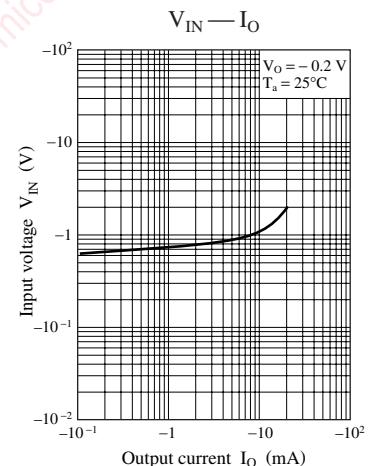
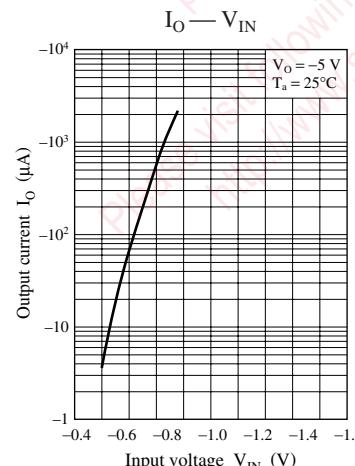
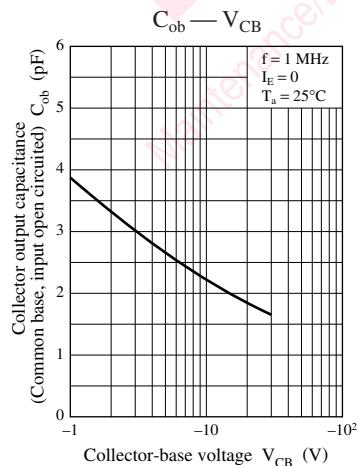
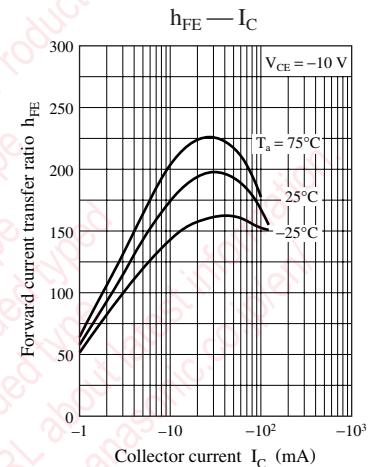
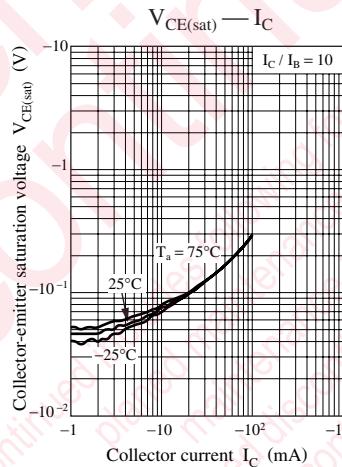
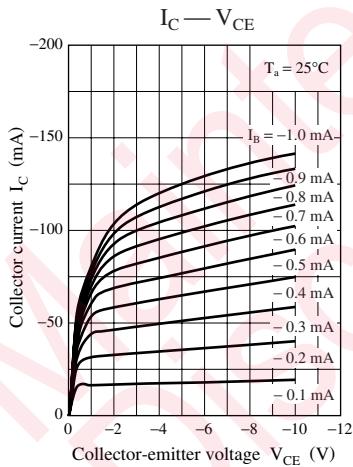


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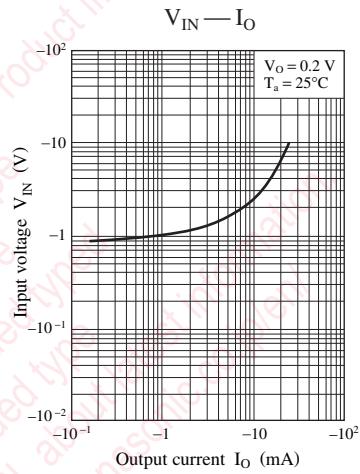
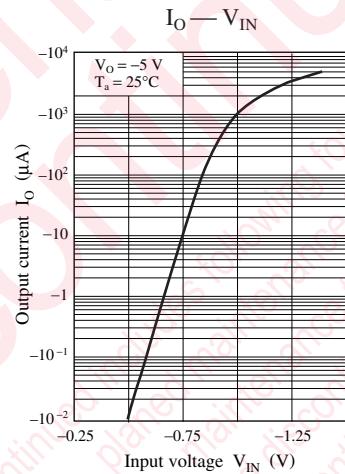
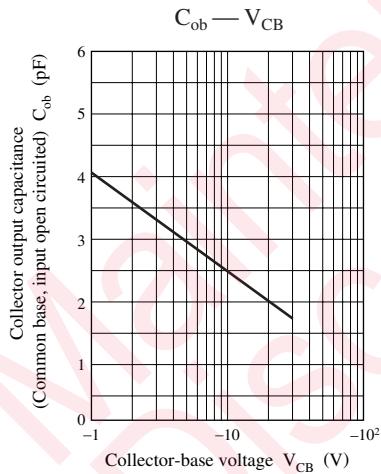
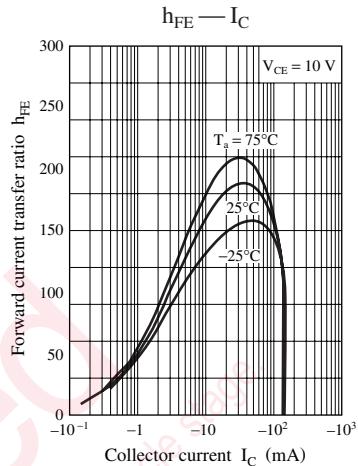
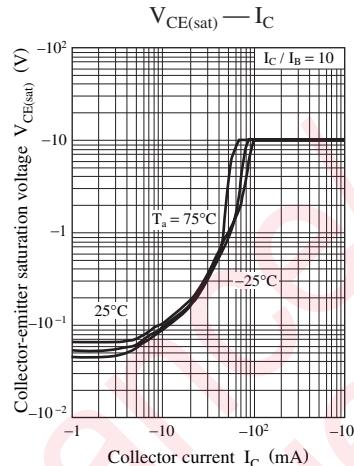
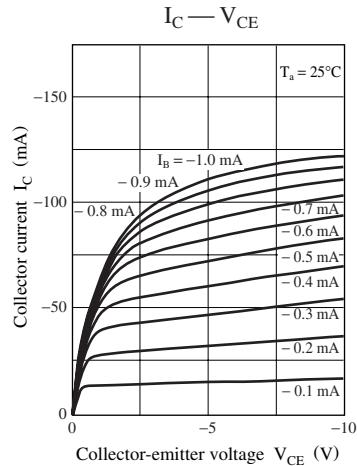




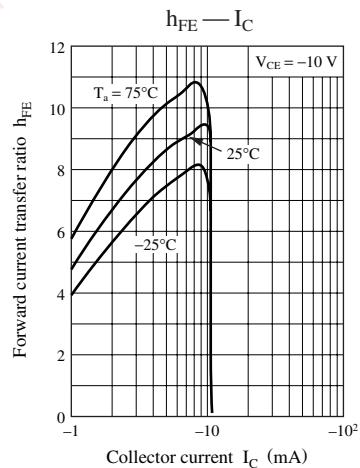
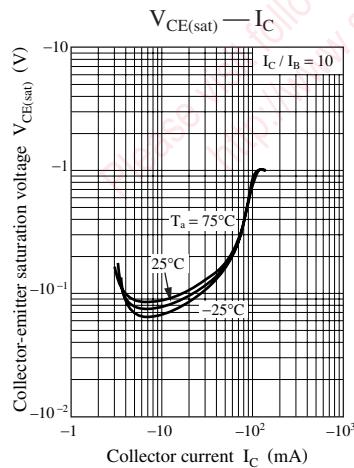
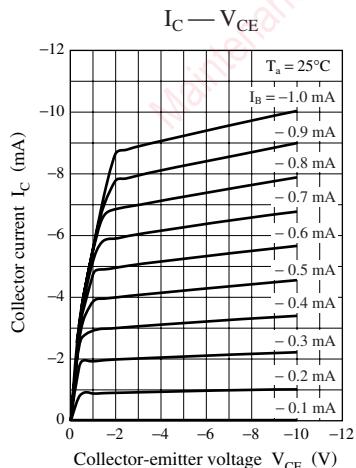
Characteristics charts of UNR911NJ

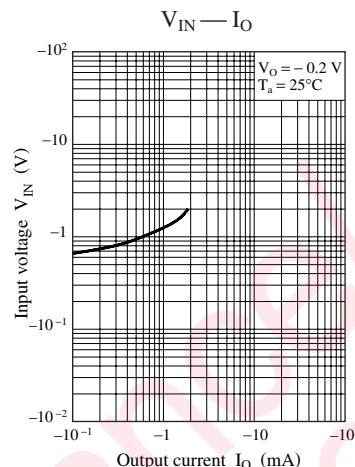
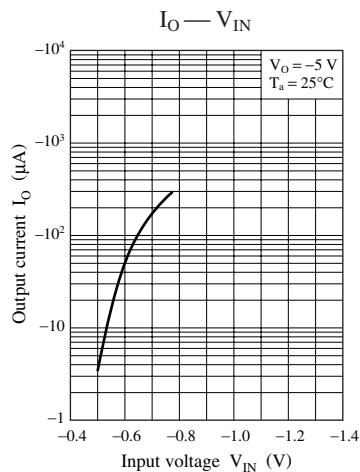


Characteristics charts of UNR911TJ



Characteristics charts of UNR911VJ





Maintained
Discontinued

Maintenance/Discontinued includes following four Product lifecycle stage.
 planned maintenance type
 planned discontinued type
 discontinued type
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